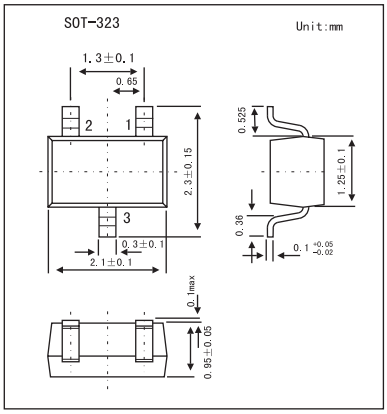
Silicon Schottky Diodes

BAT68W



Features

- For mixer applications in the VHF/UHF range
- For high speed switching

Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Value	Unit
Diode reverse voltage	V_R	8	V
Forward current	I_F	150	mA
Total power dissipation T_S = 97 ℃	P_{tot}	150	mW
Junction temperature	T_j	150	℃
Operating temperature range	T_{op}	-65 to+150	℃
Storage temperature	T_{stg}	-65 to+150	℃
Junction - ambient (Note 1)	R_{thJA}	⩽ 435	K/W
Junction - soldering point	R_{thJS}	⩽ 355	K/W

Electrical Characteristics Ta = 25℃

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Breakdown voltage	$V_{(BR)}$	$I_{(BR)}$ = 100 □A	8			V
Reverse current	I_R	V_R = 1 V, T_A = 25 ℃			0.1	μA
		V_R = 1 V, T_A = 60 ℃			1.2	
Forward voltage	V_F	I_F = 1 mA		318	340	mV
		I_F = 10 mA	340	390	500	
Diode capacitance	C_T	V_R = 1 V, f = 1 MHz			1	pF
Differential forward resistance	R_F	I_F = 5 mA			10	Ω

Marking

Marking	83s